

MT53D512M64D4HR-053 WT:D 全新原装 LPDDR4

制造商	Micron Technology
产品种类	低功耗内存存储器
无铅/环保	无铅/环保
封装	FBGA
电压电源	1.1V
存储容量	32 Gbit
工作温度	-30° C ~ 85° C

This datasheet is for LPDDR4 and LPDDR4X unified product based on LPDDR4X information. Refer to LPDDR4 setting section LPDDR4 1.10V VDDo at the end of this datasheet.

Ultra-low-voltage core and I/O power supplies

VDD1= 1.70-1.95V; 1.80V nominal

VDD2 = 1.06-1.17V; 1.10V nominal

VDDo= 1.06-1.17V; 1.10V nominal

or Low VDDQ = 0.57-0.65V; 0.60V nominal

Frequency range

2133-10 MHz (data rate range: 4266-20 Mb/s/pin)

16n prefetch DDR architecture

8 internal banks per channel for concurrent operation

Single-data-rate CMD/ADR entry

Bidirectional/differential data strobe per byte lane Programmable READ and WRITE latencies (RL/WL) Programmable and on-the-fly burst lengths (BL=16,32)

Directed per-bank refresh for concurrent bank operation and ease of command scheduling

Up to 8.5 GB/s per die

On-chip temperature sensor to control self refresh rate

Partial-array self refresh (PASR)

Selectable output drive strength (Ds) Clock-stop capability

RoHS-compliant, "green" packaging Programmable Vss (ODT) termination